Elektronische Bauelemente

D882S

NPN Plastic Encapsulated Transistor

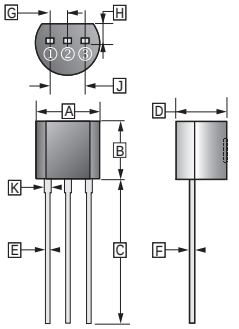
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

TO-92

FEATURES

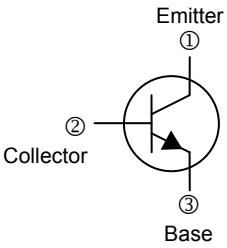
- Power Dissipation



REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	3	A
Collector Power Dissipation	P_C	625	mW
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITION
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	40	-	-	V	I_C=100 μA, I_E = 0 A
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	30	-	-	V	I_C=10 mA, I_B = 0 A
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	6	-	-	V	I_E=100 μA, I_C = 0A
Collector Cut-Off Current	I_{CBO}	-	-	1	μA	V_{CB}=40 V, I_E = 0 A
Collector Cut-Off Current	I_{CEO}	-	-	10	μA	V_{CE}=30 V, I_B = 0 A
Emitter Cut-Off Current	I_{EBO}	-	-	1	μA	V_{EB}=6 V, I_C =0 A
DC Current Gain	h_{FE}	60	-	400		V_{CE}=2 V, I_C=1 A
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.5	V	I_C=2 A, I_B=0.2 A
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	1.5	V	I_C=2 A, I_B=0.2 A
Transition Frequency	f_T	50	-	-	MHz	V_{CE} = 5 V, I_C = 0.1 A, f=10 MHz

CHARACTERISTIC CURVES

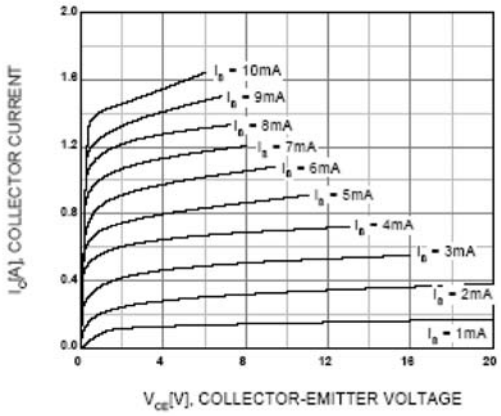


Figure 1. Static Characteristic

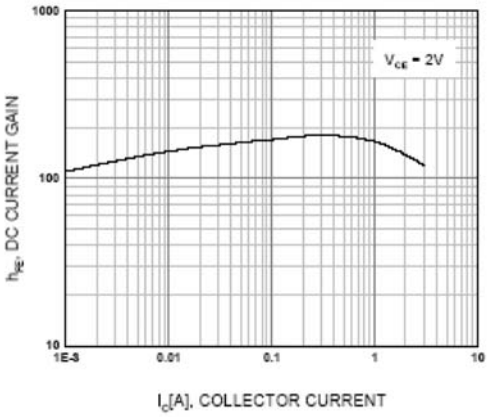


Figure 2. DC current Gain

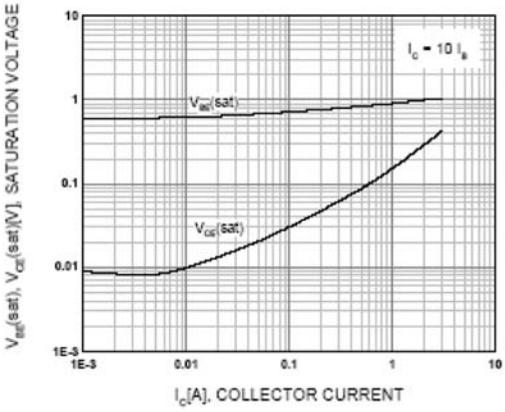


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

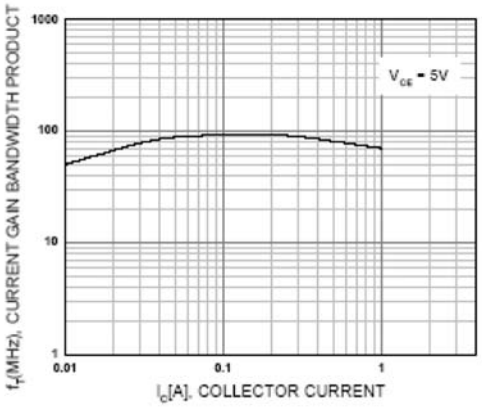


Figure 4. Current Gain Bandwidth Product

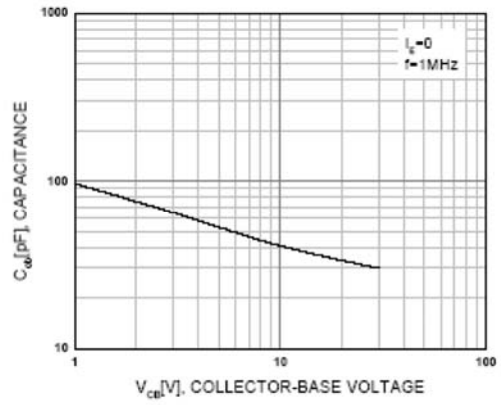


Figure 5. Collector Output Capacitance